

Alliance Memory Inc.

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Product Change Notification (PCN)

Preliminary Date: December 12th, 2016 PCN TRACKING NO:PCN-20161212102V2

Amend Date: January 5th, 2017

Subject: Product Change Notification (PCN) for Alliance SDRAM's (512M-32M x 16)

	<u>, , , , , , , , , , , , , , , , , , , </u>
Description of Change:	Product will only be offered in a new Die Revision (B die)
Reason for Change	Product revision to provide continuous support to Alliance's customers
Traceability, Guidelines (lot, date code, markings, shipment date)	Traceable through marketing part#
Updated Datasheet Summary of Changes between New and Old part numbers	Part#has been changed and updated datasheets are posted on our website http://www.alliancememory.com/products/s_dram.as See table 1 Below

Table 1

Density	Organization	Alliance Part Number	Alliance New Part Number (B die)	
512M	32M x 16	AS4C32M16SM-7TCN	AS4C32M16SB-7TCN	
512M	32M x 16	AS4C32M16SM-7TCNTR	AS4C32M16SB-7TCNTR	
512M	32M x 16	AS4C32M16SM-7TIN	AS4C32M16SB-7TIN	
512M	32M x 16	AS4C32M16SM-7TINTR	AS4C32M16SB-7TINTR	

All orders are Non-cancelable / Non-Returnable and cannot be changed.

Last Time Buy Date:	February 28 th 2017 or until stocks last as demand higher than expected
Last Time Ship Date:	June 30 th 2017
Sample Available Date	Now
PCN Effective Date:	December 12 th 2016

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Dear ValuedCustomer:

This letter provides End–of–Life (EOL) notice of SDRAM products with a 512M density. These products will move to new 'B' die in Q1-2017.

As our press release indicated a few years ago, our partnership with Micron to extend the Micron 512M SDRAM has been a great win for Alliance and our customers. The above SM parts, which are 100% identical to the Micron parts below, will allow us to continue to extend and support customers into 2017 with the Micron part marking. We hope our customers can accept both parts as they are 100% the same die/assembly and test. All done by Micron.

We will not put a PCN out on the below Micron parts but will sell them as a 'first come first serve' basis to customers. When they are out we have no choice but to only offer our customers the new drop-in replacement SB die.

The delivery deadline is June 30th, 2017 with last time buy (LTB) deadline to February 28th, 2017. Please note that the standard shipment dates will apply in general and extended delivery dates must be pre-arranged and accepted in writing by Alliance Memory Management.

Part Number	New Part Number
MT48LC32M16A2P-75 IT:C	AS4C32M16SB-7TIN
MT48LC32M16A2P-75 IT:CTR	AS4C32M16SB-7TINTR
MT48LC32M16A2P-75:C	AS4C32M16SB-7TCN
MT48LC32M16A2P-75:CTR	AS4C32M16SB-7TCNTR
MT48LC32M16A2TG-75:C	AS4C32M16SB-7TCN
MT48LC32M16A2TG-75:CTR	AS4C32M16SB-7TCNTR
MT48LC32M16A2TG-75IT:C	AS4C32M16SB-7TIN
MT48LC32M16A2TG-75IT:CTR	AS4C32M16SB-7TINTR

Please see the below a comparison chart between the SM die /Micron part vs. our new SB die. Samples/Mass production are available now.

Please contact your local Alliance Memory representative if you have any questions regarding this information.

Yours sincerely,

David Bagby

President

Alliance Memory Inc.



512M SDRAM comparison between

AS4C32M16SB-7TIN-7TCN and AS4C32M16SM-7TIN-7TCN

Part Number&result	AS4C32M16SB-7TIN	AS4C32M16SM-7TIN-7TCN	Comparison Result
Parameter		(MT48LC32M16A2P-75 IT:C)	
	AS4C32M16SB-7TCN	AS4C32M16SM-7TCN	
Wafer Process			
Power Supply	3.3±0.3V	3.3±0.3V	Same
	CLK = 143MHZ:	CLK = 133MHZ:	Difference
	Operating current - One bank	Operating current - One bank	
	Active;	Active;	
	IDD1=110mA	IDD1=110mA	
	Precharge Standby Current in	Precharge Standby Current in	
	non-power down in in	power down in in power down	
	non-power down mode	mode	
	IDD2=4mA	IDD2=3.5 mA	
	Precharge Standby Current	Standby Current in	
Typical Power	in non-power down in in		
Dissipation of Normal	non-power down mode	Active mode	
Operation	IDD2NS=36mA	IDD3=45mA	
	Precharge Standby Current in	Operating Current (Burst	
	power down in in power down	mode) IDD4=115mA	
	mode	Refresh Current	
	IDD2P=4mA	IDD5=225mA	
	Precharge Standby Current in	Self Refresh Current	
	power down in in power down	IDD7=6mA	
	mode		
	IDD2PS=4 mA		
	Active Standby Current		
	non-power down in		
	non-power down mode		
	IDD3N=60mA		
	Active Standby Current in		
	non-power down mode		
	IDD3NS=60mA		
	Operating Current (Burst		
	mode)		
	IDD4=120mA		
	Refresh Current		
	IDD5=150mA		
	Self Refresh Current		
	IDD6=4mA		
Operating	Industrial: -40°C to $+85^{\circ}\text{C}$	Industrial: -40°C to $+85^{\circ}\text{C}$	Same

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Temperature	Commercial: $0^{\circ}\!$	Commercial: $0^{\circ}\!\mathbb{C}$ to +70 $^{\circ}\!\mathbb{C}$	
Max Operating Speed	143MHz	133MHz	Difference
Interface	Input Capacitance(CI):	Input Capacitance(CI):	Difference
(Input/Output)	3.5 – 5.5 pF	2.5 – 3.8 pF	
Capacitance	Input/Output Capacitance	Input/Output Capacitance	
	(CI/O): 4- 6pF	(CI/O): 4- 6 pF	
		Input Capacitance(CLK):	
		2.5- 3.5 pF	
Interface Definition	Omit.(See datasheet)	Omit.(See datasheet)	Same.
			They are pin to
			pin.
Interface Material	Pb and Halogen Free	Pb and Halogen Free	Same
Timing Parameters	tRC>=63ns	tRC>=66ns	Difference
	tRFC>=63ns	tRFC>=66ns	
	tRCD>=21ns	tRCD>=21ns	
	tRP>=21ns	tRP>=20ns	
	tRRD>=14ns	tRRD>=15ns	
	tMRD>=14 ns	tMRD>=15 ns	
	tRAS=42~120k ns	tRAS=44~120k ns	
	tWR>=14ns	tWR>=15ns	
	tCK>=7ns	tCK>=7.5ns	
	tOH>=2.5ns	tOH>=2.7ns	
	tLZ>=0ns	tLZ>=1ns	
	tPDE>= tis+tck,	tPDE>= tck,	
	tXSR>= trc+tis ns	tXSR>=75ns	
Timing Diagram &	Omit.(See datasheet)	Omit.(See datasheet)	Same
Command			
ESD Level	Not mentioned	Not mentioned	
Capacity	512Mb	512Mb	Same
Package	54-pin 400 mil plastic TSOP II package	54-pin 400 mil plastic TSOP II package	Same
Truth Table	Omit.(See datasheet)	Omit.(See datasheet)	same